

International Conference:  
A. Semiconductor Devices

1. M M Shahidul Hassan and Orchi Hassan, "Injection Ratio and Storage Time of a Non-uniformly Doped Schottky Barrier Diode." International Conference on Electrical and Computer Engineering (ICECE), Dhaka, Bangladesh, pp. 127–130, Dec.18-20, 2012.
2. Md. Imran Momtaz and M. M. Shahidul Hassan, "Analytical expression for storage time and injection ratio of a non-uniformly doped n-Si SBD," International Conference on Devices, Circuits and Systems (ICDCS – 2012), Karuny University, Coimbatore, India, March 15-16, 2012.
3. Chowdhury, M. I. B. and Hassan, M. M. Shahidul, "Analytical modeling of base transit time considering recombination in the non-uniformly doped base," International Symposium on Humanities, Science & Engineering Research (SHUSER), Kuala Lumpur, Malaysia, pp. 117 - 122, June 05-07, 2011.
4. Islam, S.M.M., Arafat, Y, Chowdhury, I.B., Khan, M.Z.R. and Hassan, M.M.S., "Base transit time of a Heterojunction Bipolar Transistor with Gaussian doped Base," International Conference on Electrical and Computer Engineering (ICECE), Dhaka, Bangladesh, pp. 127 – 130, Dec. 18-20, 2010.
5. Chowdhury, M.I.B. and Hassan, M.M.S., "Analysis of base transit time for a bipolar junction transistor considering base current," International Conference on Electrical and Computer Engineering (ICECE), Dhaka, Bangladesh, pp. 20 - 24 , Dec. 18-20, 2010.
6. Hassan, M.M.S. and Chowdhury, M.I.B., "Effect of majority carrier current on the base transit time of a BJT for exponential doping," IEEE International Conference of Electron Devices and Solid-State Circuits (EDSSC), Hong Kong, pp. 1 – 4, Dec. 15-17, 2010.
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9. Md. Ziaur Rahman Khan, M. M. Shahidul Hassan and Touhidur Rahman, "New Expression for Base Transit Time in an Exponentially Doped Base Bipolar Transistor for All Levels of Injection," Proceedings of the 15th International Conference on Microelectronics, ICM 2003, pp. 340 - 343, December 9 -11, 2003, Cairo, Egypt, ISBN number : 977-05-2010-1, IEEE Catalog number : 03EX686.
10. A New Technique for Determining Base Transit Time of a Bipolar Junction Transistor Electrical and Computer Engineering, International Conference on Electrical and Computer Engineering (ICECE), Dhaka, Bangladesh, 19-21 Dec. 56 – 59, 2006.
11. Touhidur Rahman, M. M. Shahidul Hassan and Md. Ziaur Rahman Khan, "Analytical Model for Base Transit Time of a Bipolar Transistor with Gaussian-Doped Base," 3rd International Conference on Electrical & Computer Engineering ICECE 2004, pp. 478 – 481, Dhaka, Bangladesh, 28-30 December 2004, ISBN: 984-32-1804-4.

12. M. M. Shahidul Hassan, Md. Ziaur Rahman Khan and Touhidur Rahman, "Analytical Base Transit Time of a Bipolar Transistor Considering Field Dependent Mobility," 3rd International Conference on Electrical & Computer Engineering, ICECE 2004, pp. 482 – 485, Dhaka, Bangladesh, 28-30 December 2004, ISBN: 984-32-1804-4.
13. M. Z. Rahman Khan and M.M.S. Hassan and Touhidur Rahman, "New Expression for Base Transit Time in an Exponentially Doped Base Bipolar Transistor for All Levels of Injection," proceedings of the 15th international conference for Microelectronics (ICM03), Cairo, Egypt, 9-11 December 2003, pp 340-343.
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15. M. M. Shahidul Hassan and Ashok Kumar Karmokar, "Diffusion Capacitance of an Epitaxial High Barrier Schottky Diode," ICECE2002, 26-28 December 2002, Bangladesh, pp. 124-127.
16. Farseem M. Mohammady and M. M. S. Hassan, "A Distributed Transmission Line Model for the Base Transit Time of a nonuniformly Doped Bipolar Junction Transistor," ICECE2002, 26-28 December 2002, Bangladesh, pp. 132-135.
17. M. A. Abedin and M. M. S. Hassan, "Analytical Base Transit Time Model of a Bipolar Junction Transistor Considering Kirk Effect," IECE2002, 26-28 December 2002, Bangladesh, pp. 136-129.
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20. M. M. Shahidul Hassan, A. N. Khondker and H. Domingos, "Conduction Mechanism in BJT's during Electrical Overstress," EOS/ESD Symposium Proc., USA, pp. 280-286, 1987.
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## B. Higher Education

1. M. M. Shahidul Hassan and Omiya Hassan, “The Importance of Changing the Traditional Mode of Higher Education in Bangladesh: Creating Huge Job Opportunities for Home and Abroad”, ICEEE 2019 Vienna, Austria, 20-22 June 2019.  
<http://internationalresearchconference.org/conference/2019/06/vienna/ICEEE>
2. M. M. Shahidul Hassan, “National framework for engineering education delivery models in South Asia,” International Conference on Education Social Sciences and Humanities (SOCIO-INT15), Istanbul, Turkey, 8-10 July 2015.
3. M M Shahidul Hassan,,”Challenges and Opportunities for Engineering Education in Bangladesh,” IEOM Symposium on Global Engineering Education, December 19, 2015, Dhaka, Bangladesh..
4. M. M. Shahidul Hassan, “Outcome Based Engineering Education: A paradigm shift.” ICECE 2012 Conference, Dhaka, Bangladesh.
5. M M Shahidul Hassan, “ On Challenges of Implementing Outcome Based Engineering Education in Universities in Bangladesh”, pp. 362 – 364, 20-22 Dec. 2012.
6. M. M. Shahidul Hassan, “Implementing Outcome Based Engineering Education in Bangladesh,” Advanced Education and Management [ICAEM2014], Jan 04 –Jan 06 2014, Beijing, China